

D2S4M

Schottky Barrier Diodes

40V, 2A

Feature

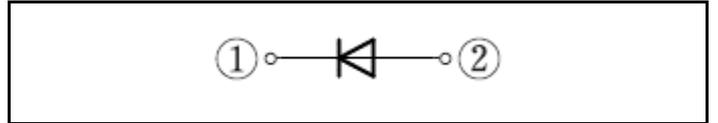
- High Recovery Speed
- Low V_F
- Pb free terminal
- RoHS:Yes

OUTLINE

Package (House Name): AX078



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tl=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-40 to 150	°C
Junction temperature	Tj		-40 to 150	°C
Repetitive peak reverse voltage	V _{RRM}		40	V
Repetitive peak surge reverse voltage	V _{RRSM}	Pulse width 0.5ms, duty=1/40	45	V
Average forward current	I _{F(AV)}	50Hz sine wave, Resistance load, Tl=122°C ※	2	A
Average forward current	I _{F(AV)}	50Hz sine wave, Resistance load, Ta=36°C ※	1.5	A
Surge forward current	I _{FSM}	50Hz sine wave, Non-repetitive, 1 cycle, Peak value, Tj=25°C	60	A
Repetitive peak surge reverse power	P _{RRSM}	Pulse width 10μs, Tj=25°C	160	W

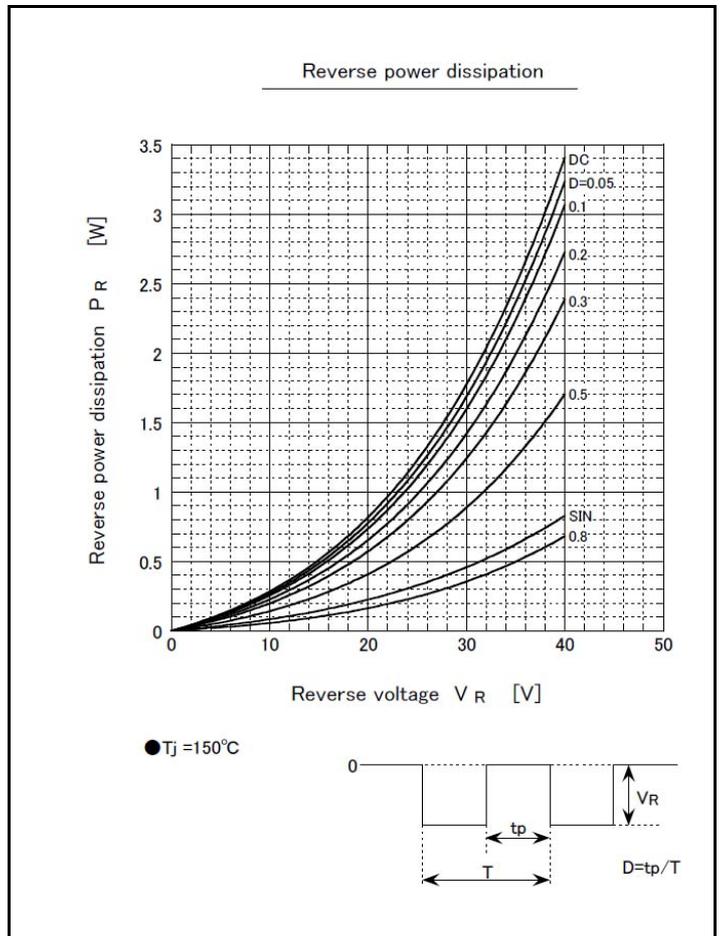
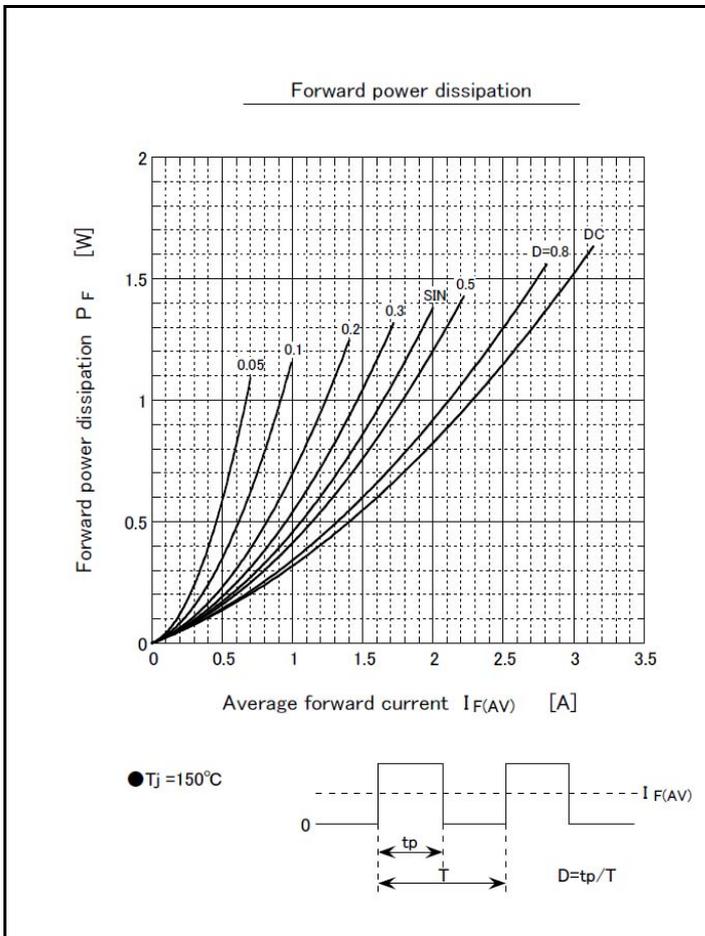
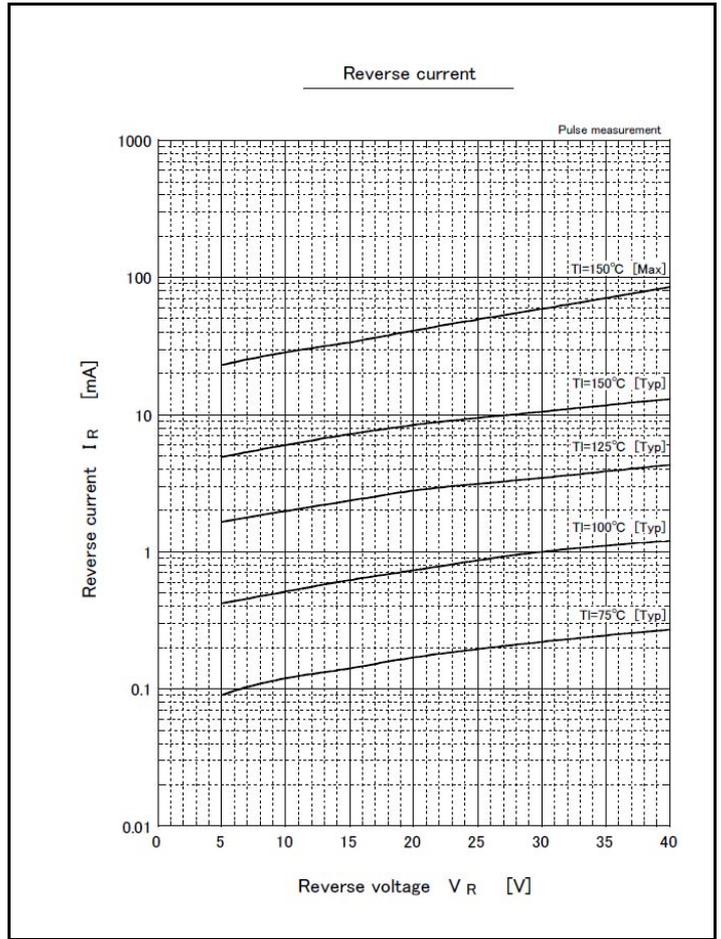
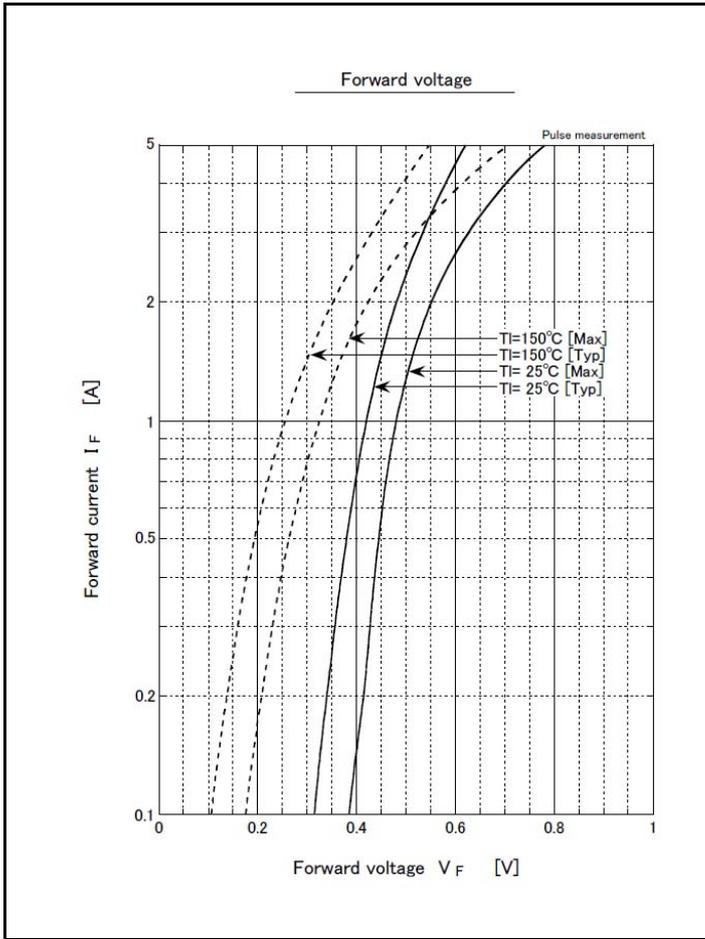
※ : See the original Specifications

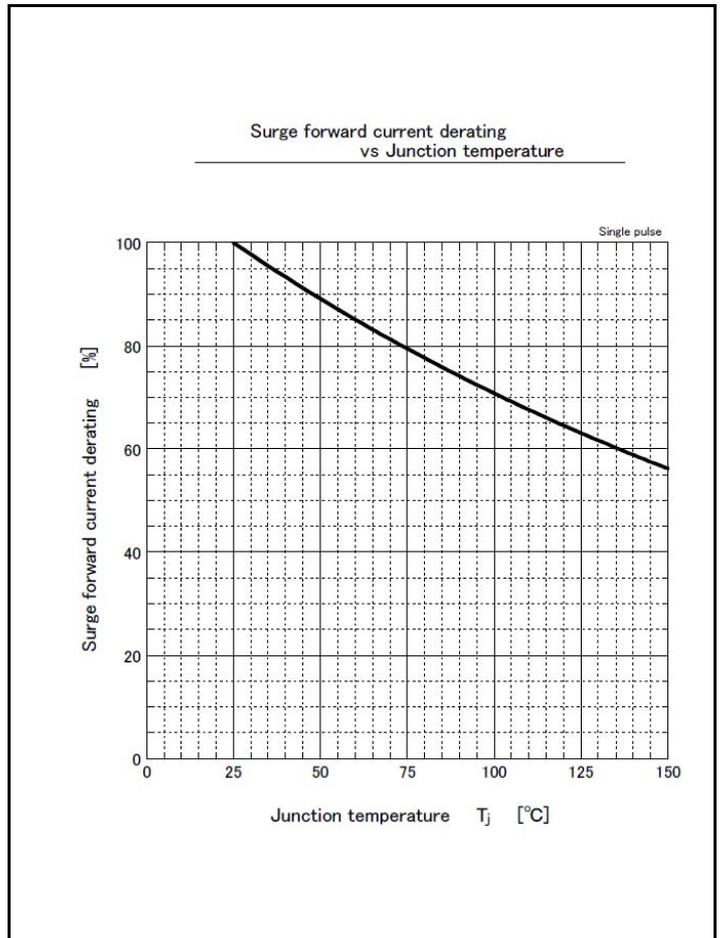
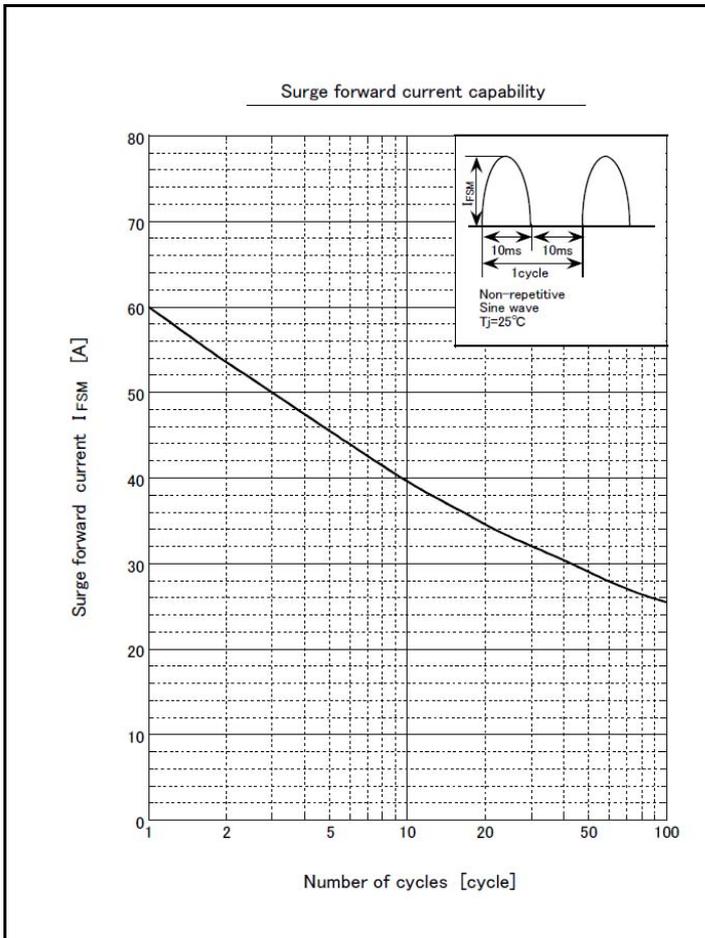
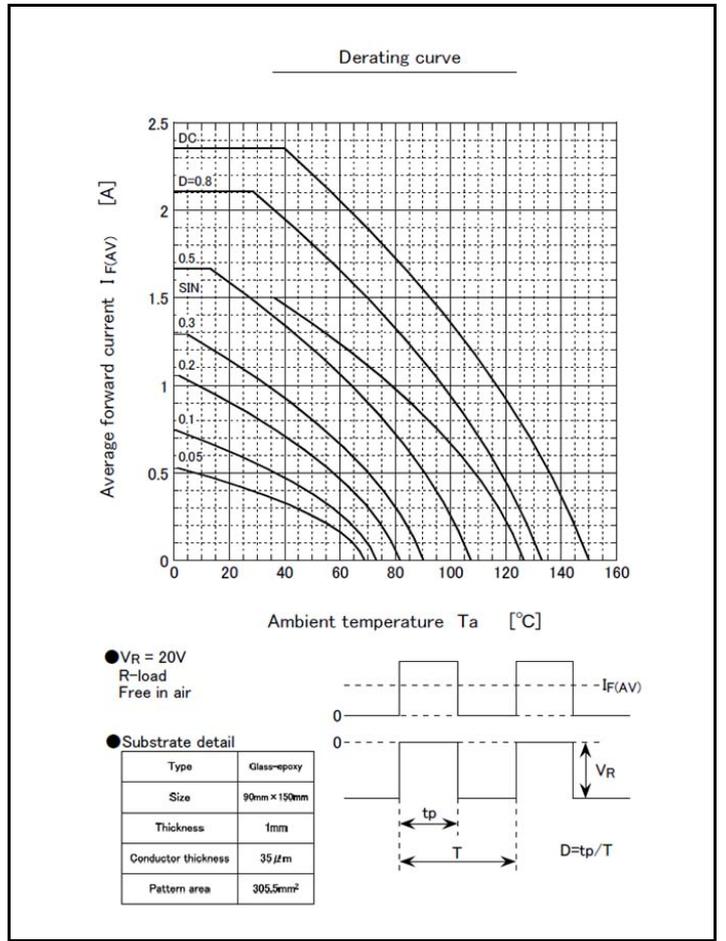
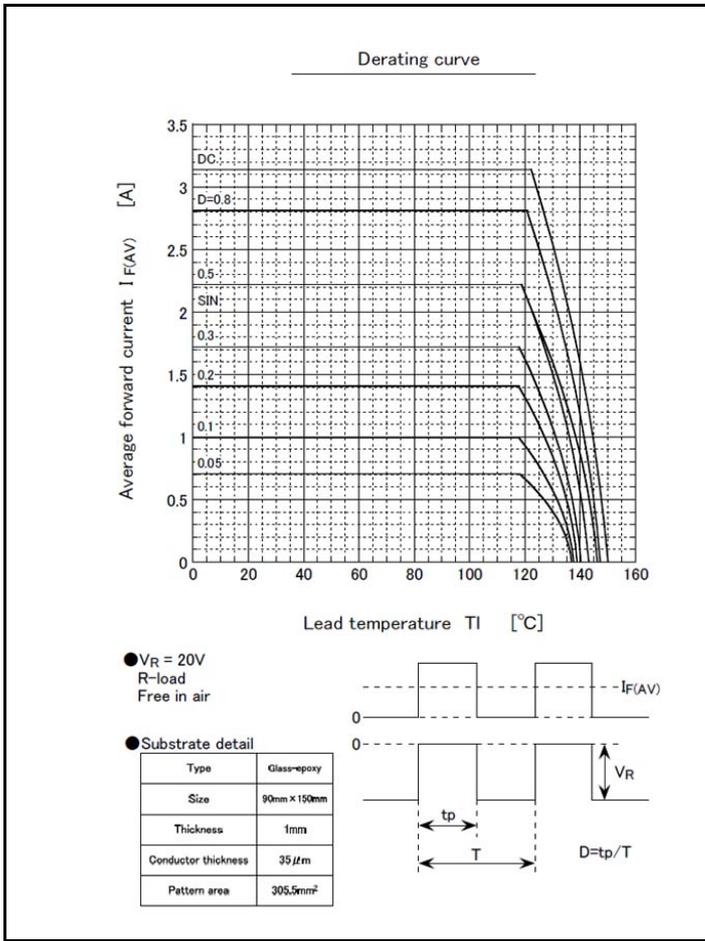
Electrical Characteristics (unless otherwise specified : Tl=25°C)

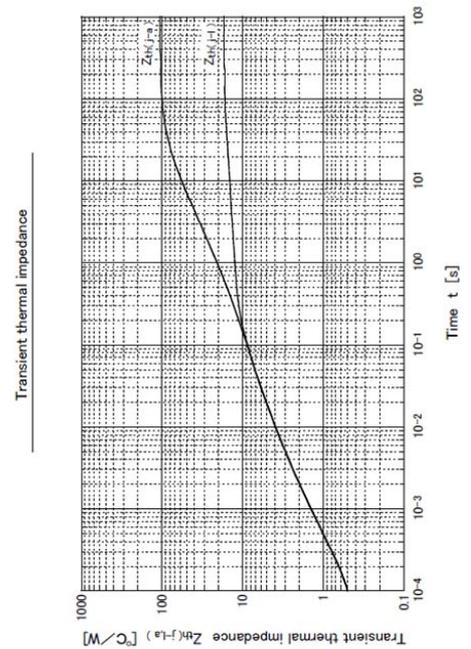
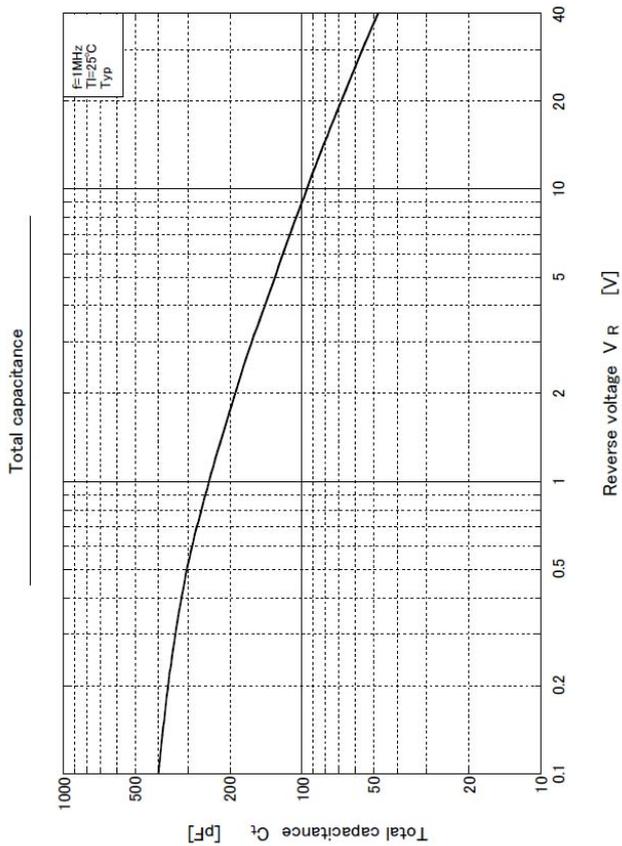
Item	Symbol	Conditions	Ratings			Unit
			MIN	TYP	MAX	
Forward voltage	V_F	$I_F=2A$, Pulse measurement			0.55	V
Reverse current	I_R	$V_R=40V$, Pulse measurement			2	mA
Total capacitance	C_t	$f=1MHz$, $V_R=10V$		95		pF
Thermal resistance	$R_{th(j-l)}$	Junction to lead, On glass-epoxy substrate *			17	°C/W
Thermal resistance	$R_{th(j-a)}$	Junction to ambient, On glass-epoxy substrate *			105	°C/W

* :See the original Specifications

CHARACTERISTIC DIAGRAMS



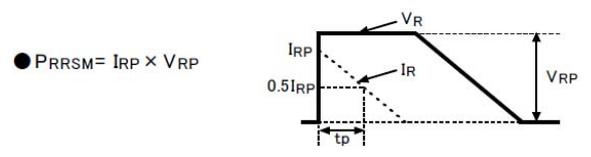
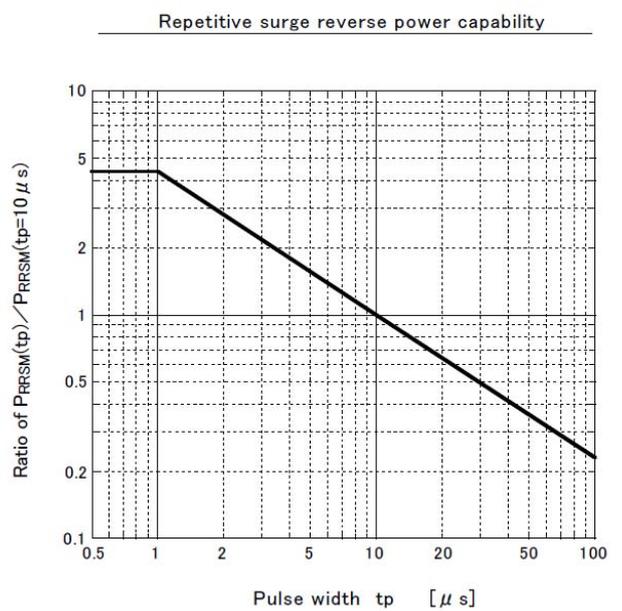
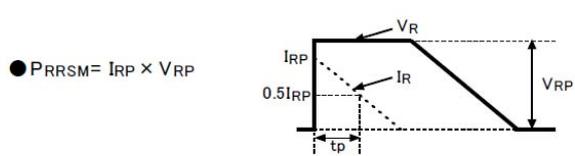
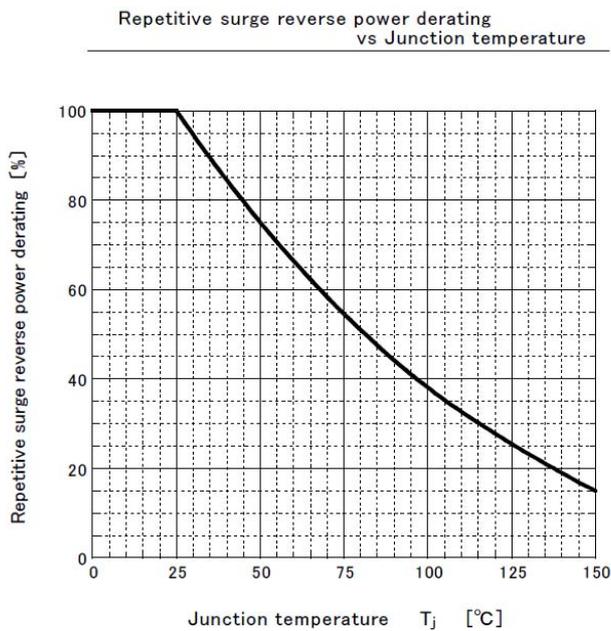




● Substrate detail

Type	Glass-epoxy
Size	90mm X 150mm
Thickness	1mm
Conductor thickness	35μm
Pattern area	3055mm ²

● TI sensing point



Outline Dimensions

unit:mm

scale: 2/1

A4

JEDEC Code	—
JEITA Code	—
House Name	AX078

